

30V P-Channel Power MOSFET

MOSFET

Metal Oxide Semiconductor Field Effect Transistor

HRT4407 Data Sheet

Rev. 2020 V3.0



南京华瑞微集成电路有限公司 NanJing HRM Semiconductor Co.,Ltd



HRT4407

Pin1

30V P-Channel Power MOSFET

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Description

P-Channel Power MOSFET designed by HR-Micro Semiconductor Company, according to the advanced Trench Technology. This devices provide an excellent gate charge and $R_{DS(on)}$, which leads to extremely communication and conduction losses. So it is very suitable for AC/DC power conversion, Lighting, and industrial power applications. The package form is SOP-8 which accords with the RoHS standard.

Features

- Low FOM R_{DS(on)}×Q_{gd}
- 100% avalanche tested
- Easy to use/drive
- RoHS compliant

Applications

- Power Switch Circuit of Adaptor and Charger
- Battery Protection Charge/Discharge
- Notebook AC-in Load Switch



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SOP-8



Key Performance Parameters

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Parameter	Value	Unit		
V _{DS@ TA=25°C}	-30	V		
R _{DS(on),max@-10V}	12.5	mΩ		
R _{DS(on),max@-4.5V}	19.5	mΩ		
Q _{g,typ}	62	nC		
I _{D@TA=25°C}	-14	А		
$I_{D,pulse}$	-56	А		
E _{AS} ¹⁾	160	mJ		
Device Marking and Package Information				
Device	Package	Marking		

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SOP-8



Absolute Maximum Ratings $T_A = 25^{\circ}C$, unless otherwise noted						
Parameter Drain-Source Voltage(V _{GS} =0V)		Symbol	Values -30	Unit V		
		V _{DS}				
Continuous Drain Current ²⁾	T _A = 25°C	- I _D -	-14	A		
	T _A = 100°C		-8.8			
Pulsed Drain Current ³⁾		I _{D,pulse}	-52	А		
Gate-Source Voltage		V _{GSS}	±25	V		
Single Pulse Avalanche Energy		E _{AS}	160	mJ		
Power Dissipation		P _D	2.9	W		
Operating Junction and Storage Temperature Range		T _J , T _{stg}	-55~+150	°C		

Thermal Resistance					
Parameter	Symbol	Max.	Unit		
Thermal Resistance, Junction-to-Ambient	R _{thJA}	42	°C/W		

Notes

1) L=0.5mH, V_{DD}=-15V, Start T_J=25°C.

2) Limited by maximum junction temperature.

3) Repetitive Rating: Pulse width limited by maximum junction temperature.



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Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static Characteristics							
Drain-Source Breakdown Voltage	V _{(BR)DSS}	$V_{GS} = 0V, I_{D} = -250\mu A$	-30			V	
Zero Gate Voltage Drain Current		V _{DS} = -30V V _{GS} = 0V, T _J = 25°C			-1	- μΑ	
	I _{DSS}	V _{DS} = -30V V _{GS} = 0V, T _J = 125°C			-100		
Gate-Source Leakage Current	I _{GSS}	$V_{GS} = \pm 25V$			±100	nA	
Gate-Source Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_D = -250 \mu A$	-1.2	-1.7	-2.3	V	
		V_{GS} = -20V, I_{D} = -14A		9	11.5	mΩ	
Drain-Source On State Posistance	R	V_{GS} = -10V, I_{D} = -14A		10	12.5	mΩ	
Drain-Source On-State-Resistance	R _{DS(on)}	V_{GS} = -6V, I_{D} = -10A		12	15	mΩ	
		V _{GS} = -4.5V, I _D = -10A		14.5	19.5	mΩ	
Dynamic Characteristics							
Input Capacitance	C _{iss}	V _{GS} = 0V, V _{DS} = -15V f = 1.0MHz		2941		pF	
Output Capacitance	C _{oss}			325			
Reverse Transfer Capacitance	C _{rss}			297			
Total Gate Charge	Q _g			62		nC	
Gate-Source Charge	Q_gs	V _{DS} = -15V, I _D = -14A		10.4			
Gate-Drain Charge	Q _{gd}	$V_{GS} = -10V$		11.8			
Gate Plateau Voltage	V _{Plateau}			3.2		V	
Turn-on Delay Time	t _{d(on)}			12			
Turn-on Rise Time	t _r	V _{DS} = -15V, V _{GS} = -10V		7		ns.	
Turn-off Delay Time	$t_{d(off)}$	$R_{G} = 3\Omega$, $I_{D} = -14A$		53			
Turn-off Fall Time	t _f			16.5			
Drain-Source Body Diode Character	istics						
Body Diode Forward Voltage	V _{SD}	$T_{J} = 25^{\circ}C, I_{SD} = -14A$ $V_{GS} = 0V$		-0.7	-1.2	V	
Continuous Diode Forward Current	I _S				-13	А	
Reverse Recovery Time	t _{rr}			18		ns	
Reverse Recovery Charge	Q _{rr}	$I_F = -14A, di_F/dt = -100A/\mu s$		32		nC	

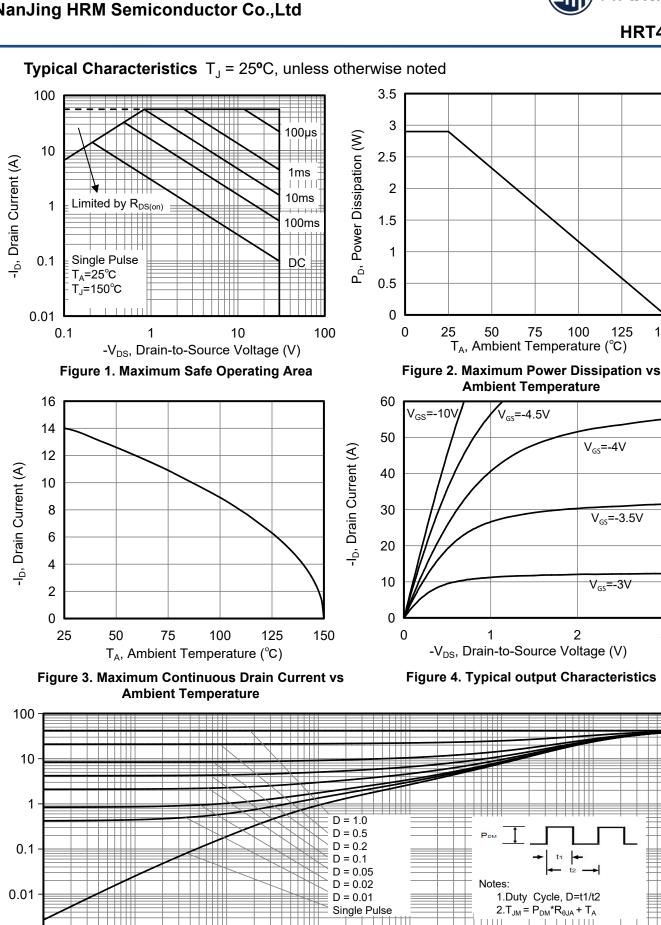


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150

3

10



0.1

0.000001

0.00001

0.0001

0.001

Z0JA, Thermal Response (°C/W)

Figure 5. Maximum Effective Thermal Impedance, Junction to Ambient

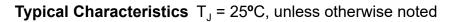
T, Rectangular Pulse Duration (sec)

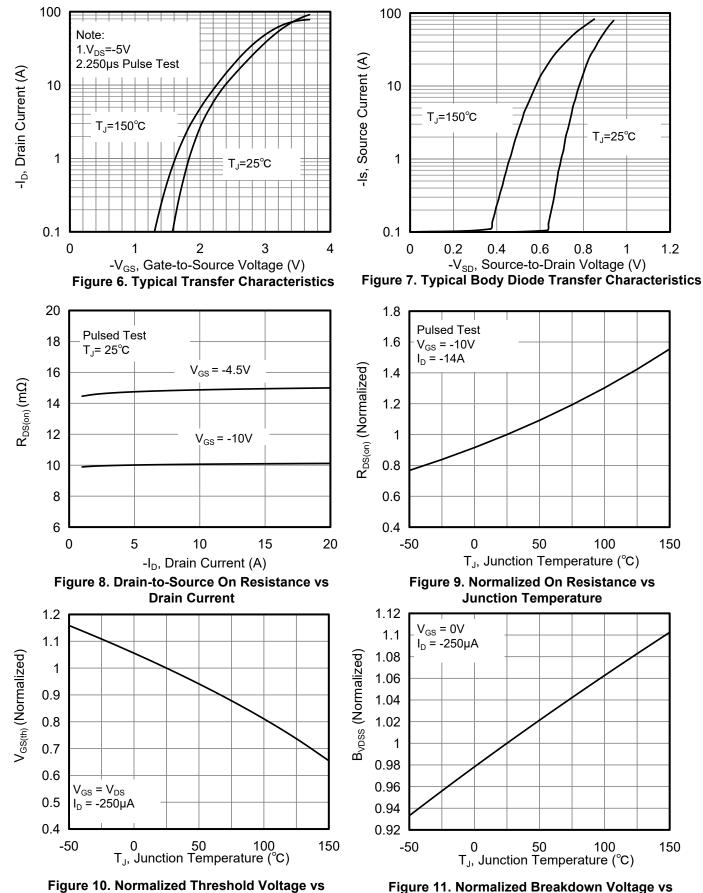
0.01

0.001

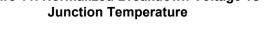
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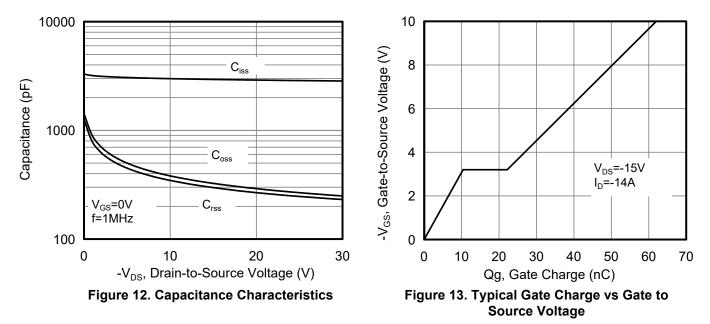


Junction Temperature





Typical Characteristics $T_J = 25^{\circ}C$, unless otherwise noted







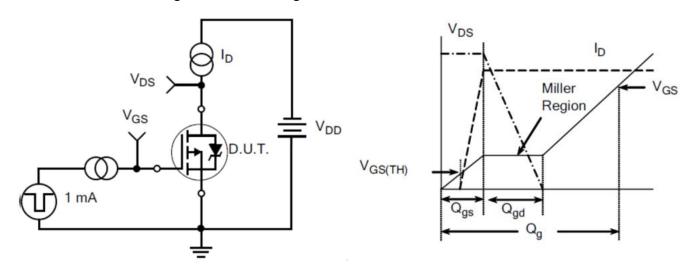
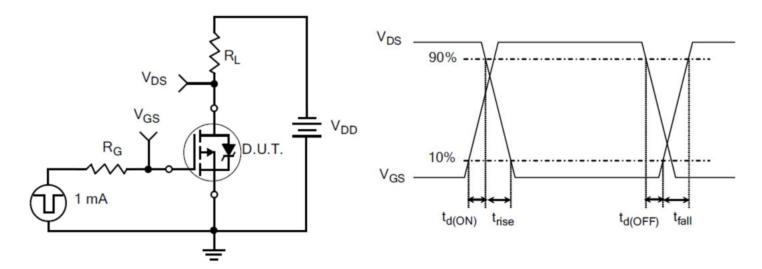
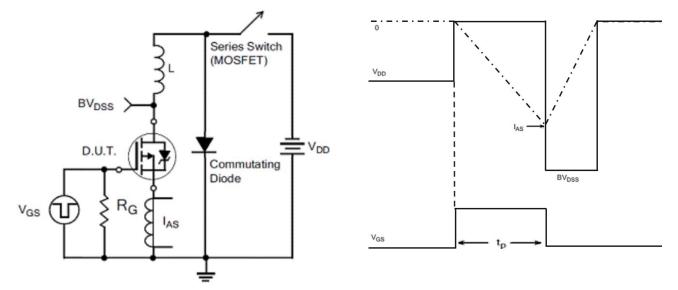


Figure B: Resistive Switching Test Circuit and Waveform



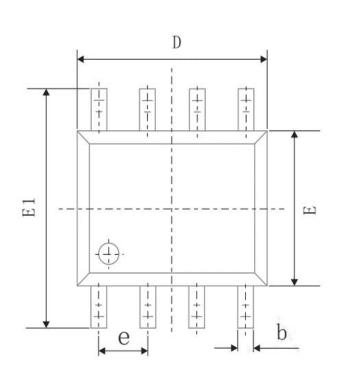


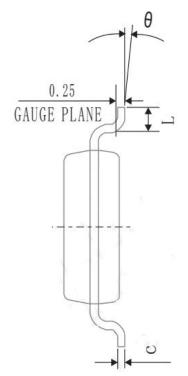


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Outlines SOP-8 Package





COMMON DIMENSIONS (UNITS OF MEASURE=mm)

SYMBOL	MIN	NOM	MAX
А	1.35	1.575	1.8
A1	0.05	0.165	0.25
A2	1.25	1.4125	1.55
b	0.3	0.425	0.51
С	0.153	0.2115	0.253
D	4.8	4.9	5
E	3.8	3.9	4
E1	5.8	6	6.2
L	0.45	0.71	1
θ	0°	4°	8°
е	1.27 BSC		



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